

Growth of Topological Bi_{2-x}Sb_xSe₃ Single Crystals

Matt Curtis, Zhenyu Diao, Jordan Ball, Dana Browne, Rongying Jin

Department of Physics and Astronomy, Louisiana State University, Baton Rouge

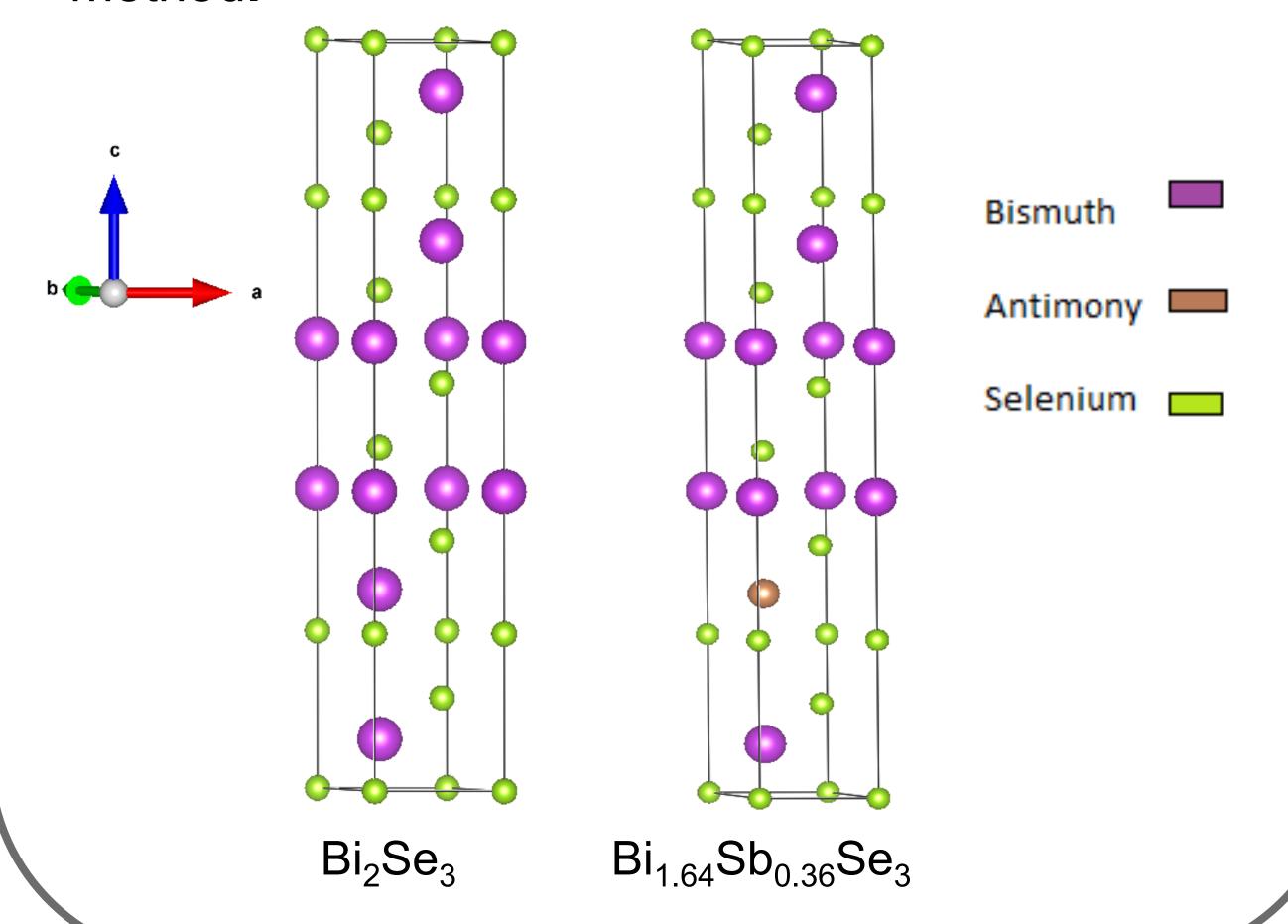


Abstract

In order to study the topological properties of Bi_{2-x}Sb_xSe₃, we need to grow high quality single crystals. These high quality single crystals allow us to measure the crystal's conducting outer layer and insulating inner bulk. This type of structure is characteristic of a topological insulator.

Introduction

Topological insulators have been the attention of many condensed matter studies recently. One such crystal is Bi₂Se₃. My research is to grow and analyze such crystals with different doping of antimony, Bi_{2-x}Sb_xSe₃, to see how its physical properties change with doping using the self flux method.

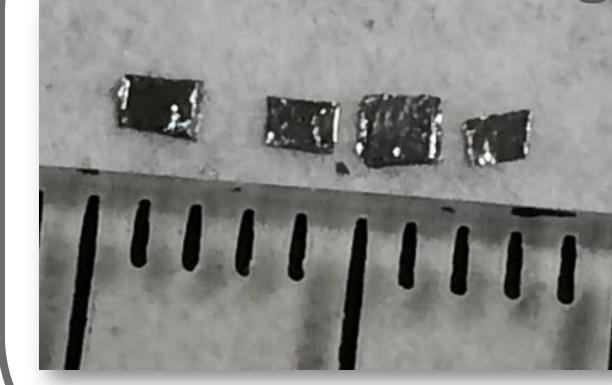


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Single Crystals



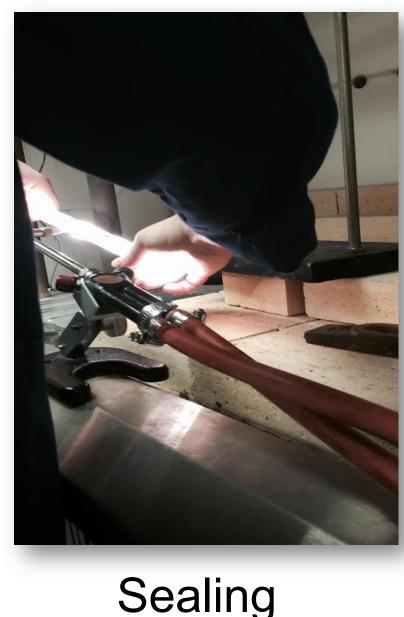
Bi₂Se₃



 $Bi_{1.64}Sb_{0.36}Se_3$

Procedure

- Weigh starting materials with appropriate ratio
- Mix the starting materials
- Put the mixture in crucible and seal in silica tube (15mTorr)

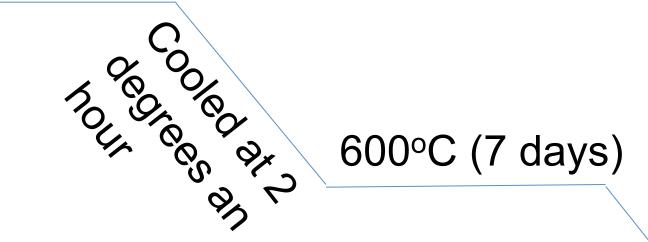




Sealed

Use a box furnace to cook and anneal

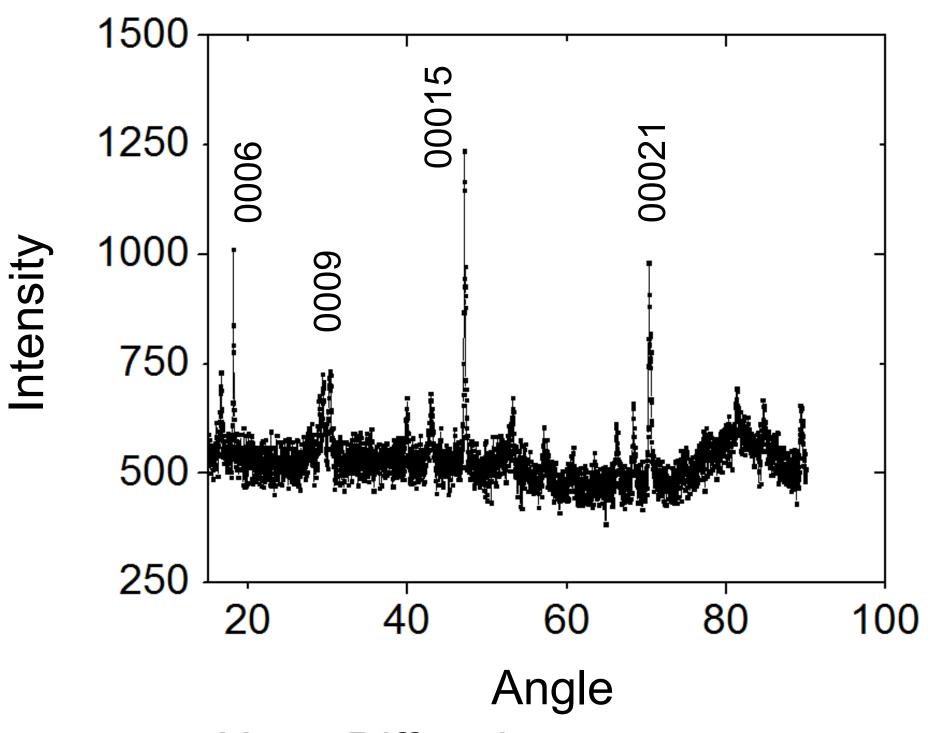
770°C (48 hours)



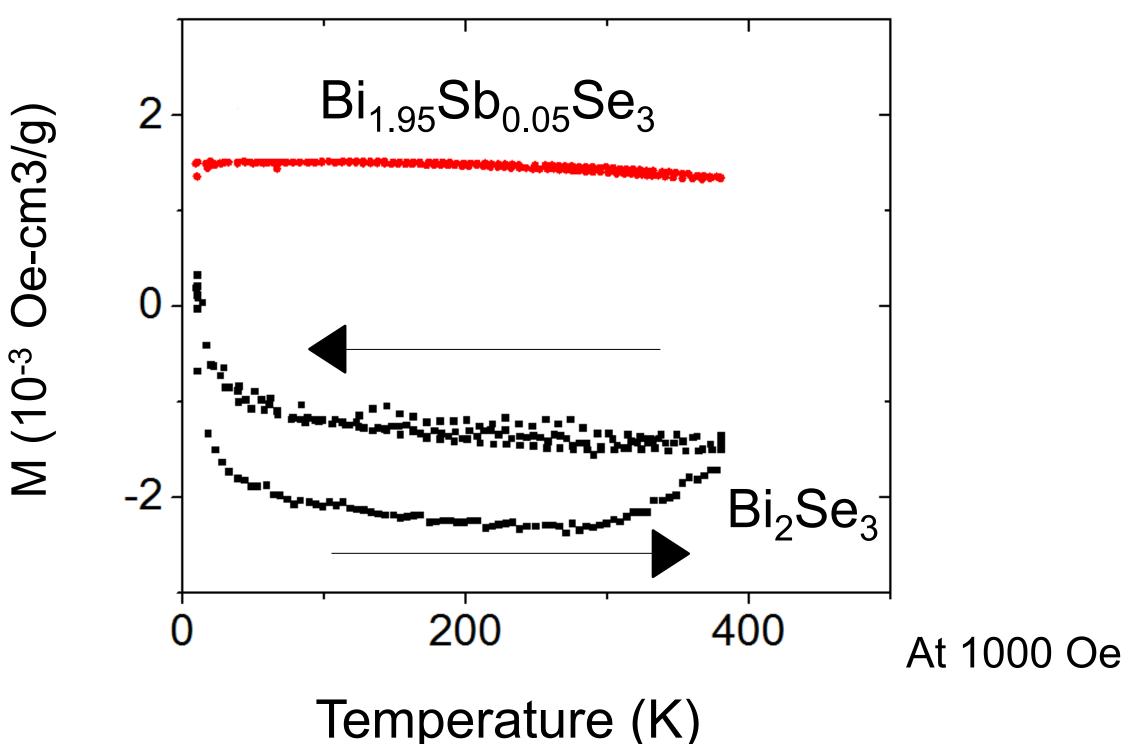
Summary

- We have successfully grown Bi_{2-x}Sb_xBi₃ single crystals with different doping levels
- The temperature dependence of magnetization shows that Bi_{2-x}Sb_xSe₃ is paramagnetic
- The field dependence of magnetization at 2 K indicates that there is some ferromagnetic interaction at low temperatures

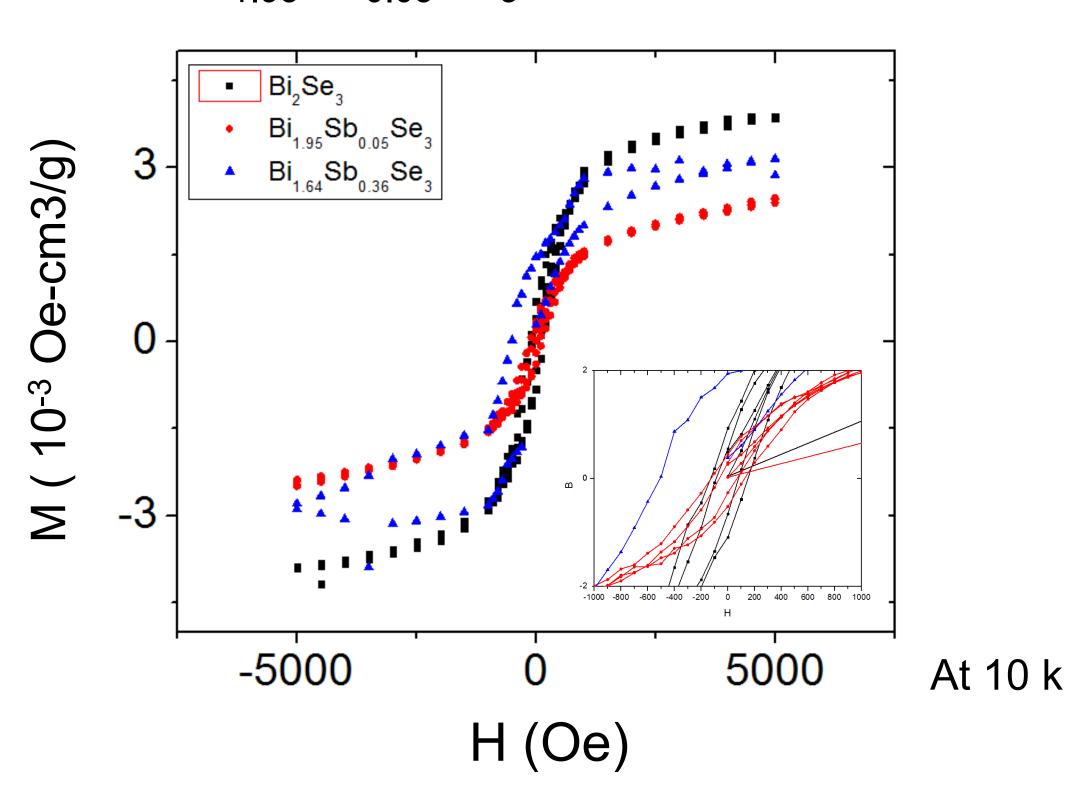
Properties



X-ray Diffraction



- Bi₂Se₃: diamagnetic, hysteretic
- Bi_{1.95}Sb_{0.05}Se₃: paramagnetic



- Bi₂Se₃: no hysteresis
 Bi_{1.95}Sb_{0.05}Se₃ and Bi_{1.64}Sb_{0.36}Se₃: hysteretic